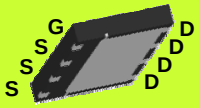
N-Channel

CICLON NexFET™ Power MOSFETs

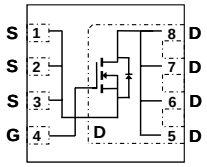
CSD16406Q3

Features

- Ultra Low Qg & Qgd
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free



QFN 3.3mm x 3.3mm Plastic Package



Top View

Product Summary

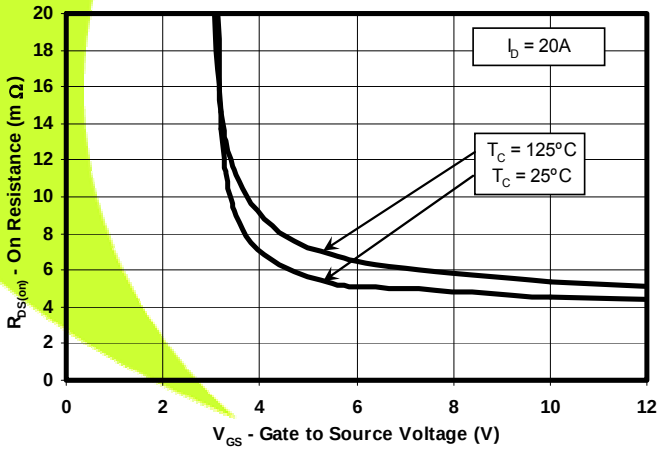
V_{DS}	25		V
Q_g	5.8		nC
Q_{gd}	1.5		nC
$R_{DS(on)}$	V_{GS}=4.5V	5.9	mΩ
	V_{GS}=10V	4.2	mΩ
V_{th}	1.7		V

Maximum Values (T_A=25°C unless otherwise stated)

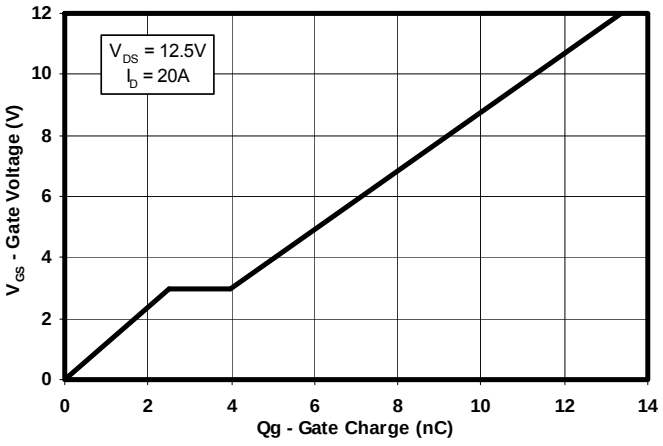
Symbol	Parameter	Value	Units
V_{DS}	Drain to Source Voltage	25	V
V_{GS}	Gate to Source Voltage	+16 / -12	V
I_D	Continuous Drain Current, T_C = 25°C	60	A
	Continuous Drain Current[1]	19	A
I_{DM}	Pulsed Drain Current, T_A = 25°C[2]	114	A
P_D	Power Dissipation[1]	2.7	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
E_{AS}	Avalanche Energy, single pulse I_D =45A, L = 0.1mH, R_G = 25Ω	101	mJ

1. Rθja = 46°C/W on 1in² Cu (2 oz.) on 0.060" thick FR4 PCB.
2. Pulse width ≤300 µs, duty cycle ≤ 2%

$R_{DS(ON)}$ vs. V_{GS}



Gate Charge



Ordering Information

Type	Package	Package Media	Qty	Ship
CSD16406Q3	QFN 3.3 X 3.3 Plastic Package	13 inch reel	2500	Tape and Reel

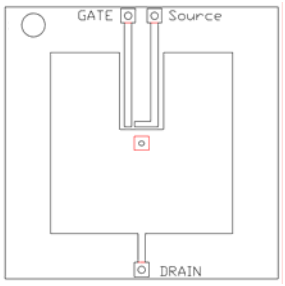
Electrical Characteristics (T_A = 25°C unless otherwise stated)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Static Characteristics						
BV_{DSS}	Drain to Source Voltage	V_{GS} = 0V, I_D = 250µA	25	—	—	V
I_{DSS}	Drain to Source Leakage Current	V_{GS} = 0V, V_{DS} = 20V	—	—	1	µA
I_{GSS}	Gate to Source Leakage Current	V_{DS} = 0V, V_{GS} = +16/-12V	—	—	100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{DS} = V_{GS}, I_D = 250µA	1.4	1.7	2.2	V
$R_{DS(on)}$	Drain to Source On Resistance	V_{GS} = 4.5V, I_D = 20A	—	5.9	7.4	mΩ
		V_{GS} = 10V, I_D = 20A	—	4.2	5.3	mΩ
g_{fs}	Transconductance	V_{DS} = 15V, I_D = 20A	—	53	—	S
Dynamic Characteristics						
C_{ISS}	Input Capacitance	V_{GS} = 0V, V_{DS} = 12.5V f = 1MHz	—	840	1100	pF
C_{OSS}	Output Capacitance		—	680	950	pF
C_{RSS}	Reverse Transfer Capacitance		—	57	80	pF
R_g	Series Gate Resistance		—	1.4	—	Ω
Q_g	Gate Charge Total (4.5V)	V_{DS} = 12.5V, I_D =20A	—	5.8	8.1	nC
Q_{gd}	Gate Charge Gate to Drain		—	1.5	—	nC
Q_{gs}	Gate Charge Gate to Source		—	2.5	—	nC
$Q_{g(th)}$	Gate Charge at Vth		—	1.5	—	nC
Q_{OSS}	Output Charge	V_{DS} = 13.6V, V_{GS} = 0V	—	13.9	—	nC
$t_{d(on)}$	Turn On Delay Time	V_{DS} = 12.5V V_{GS} = 4.5V I_D = 20A R_G = 7.5 Ω	—	10.4	—	ns
t_r	Rise Time		—	20	—	ns
$t_{d(off)}$	Turn Off Delay Time		—	9.4	—	ns
t_f	Fall Time		—	29	—	ns
Diode Characteristics						
V_{SD}	Diode Forward Voltage	I_S = 20A, V_{GS} = 0V	—	0.85	1.0	V
Q_{rr}	Reverse Recovery Charge	V_{dd}=13.6V, I_F = 20A, di/dt = 300A/µs	—	18	—	nC
t_{rr}	Reverse Recovery Time	V_{dd}=13.6V, I_F = 20A, di/dt = 300A/µs	—	22	—	ns

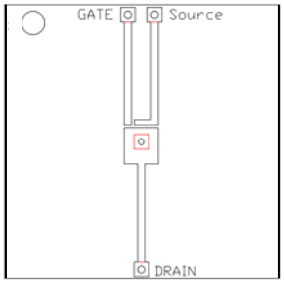
Thermal Characteristics (T_A = 25°C unless otherwise stated)

Symbol	Parameter	Min	Typ	Max	Units
Thermal Characteristics					
$R_{\theta JC}$	Thermal Resistance Junction to Case[3]	—	—	2.7	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient[3,4]	—	—	58	°C/W

3. $R_{\theta jc}$ is determined with the device mounted on a 1in square 2 oz. Cu pad on a 1.5x1.5 in .060in thick FR4 board. $R_{\theta jc}$ is guaranteed by design while $R_{\theta ca}$ is determined by the user's board design.
4. Device mounted on FR4 Material with 1in^2 of 2 oz. Cu.



Max Rθja =58 °C/W when mounted on 1in^2 of 2 oz. Cu.



Max Rθja =162 °C/W when mounted on min pad area of 2 oz. Cu.

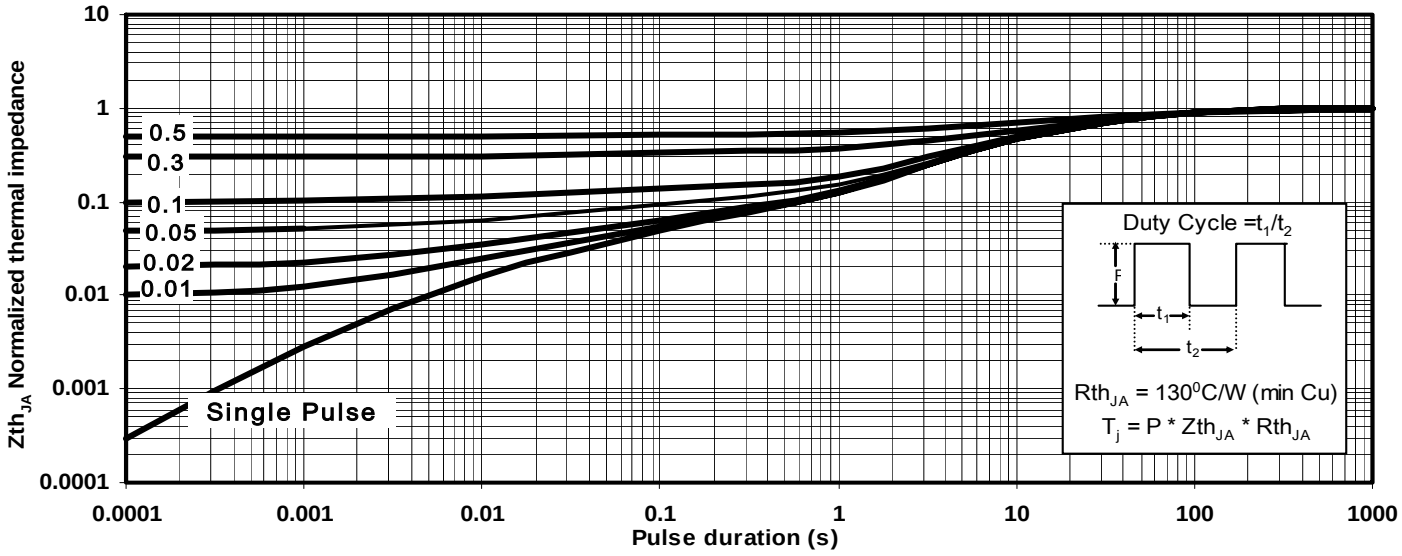


Figure 1: Transient Thermal Impedance

Typical MOSFET Characteristics (T_A = 25°C unless otherwise stated)

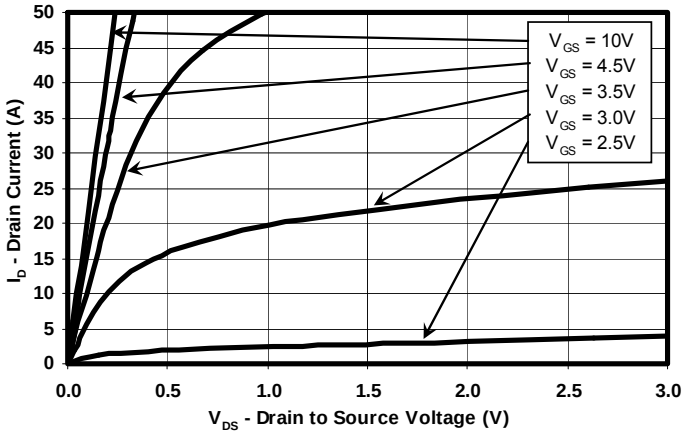


Figure 2: Saturation Characteristics

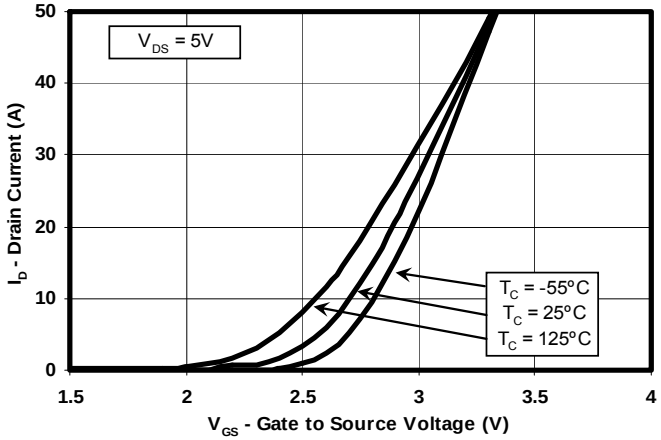


Figure 3: Transfer Characteristics

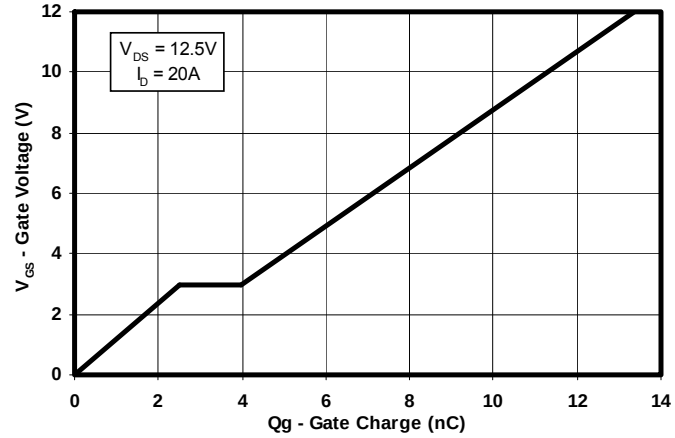


Figure 4: Gate Charge

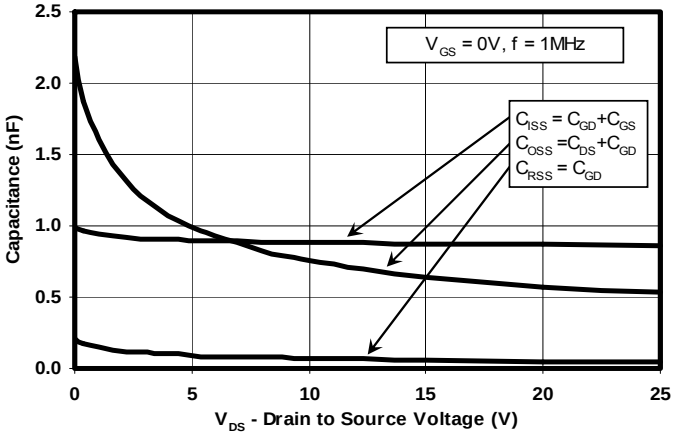


Figure 5: Capacitance

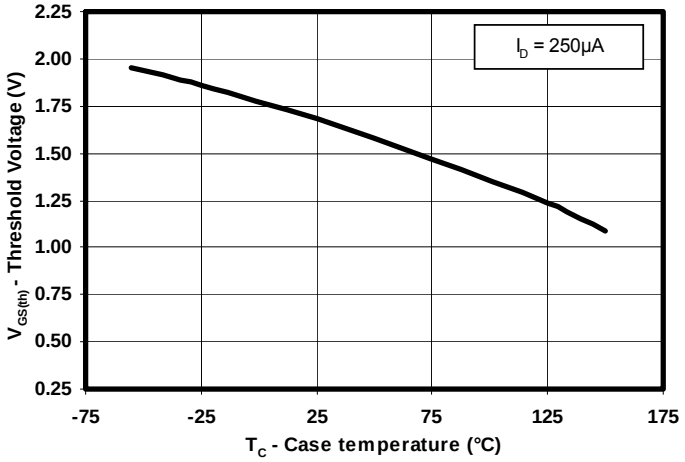


Figure 6: Threshold Voltage vs. Temperature

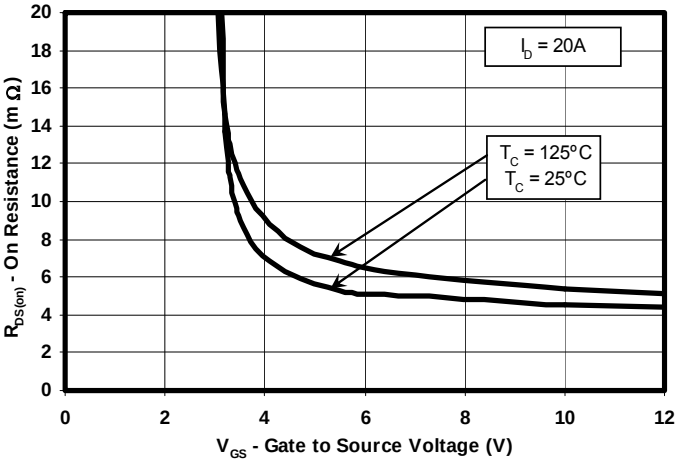


Figure 7: On Resistance vs. Gate Voltage

Typical MOSFET Characteristics (T_A = 25°C unless otherwise stated)

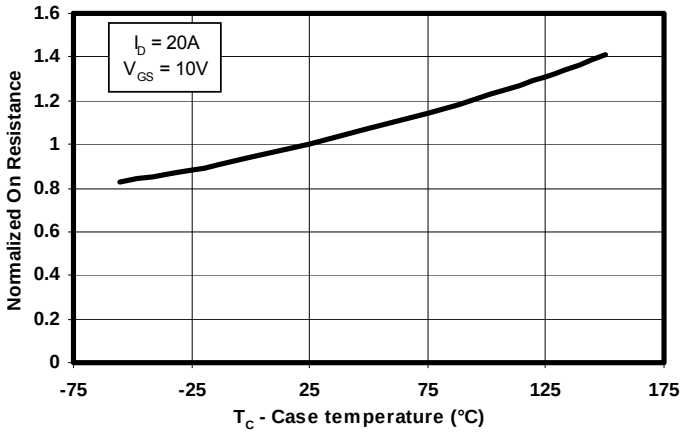


Figure 8: On Resistance vs. Temperature

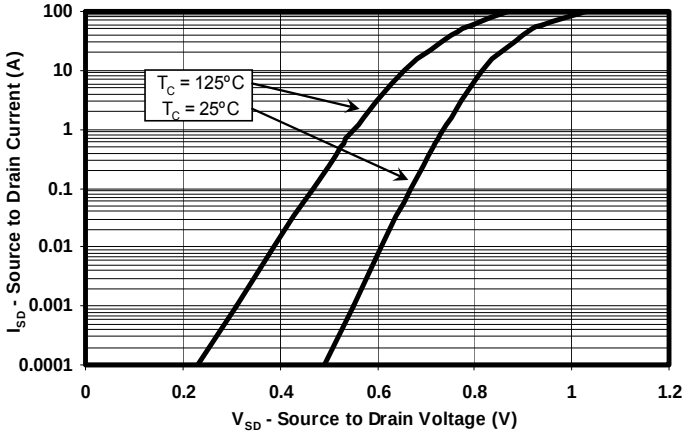


Figure 9: Typical Diode Forward Voltage

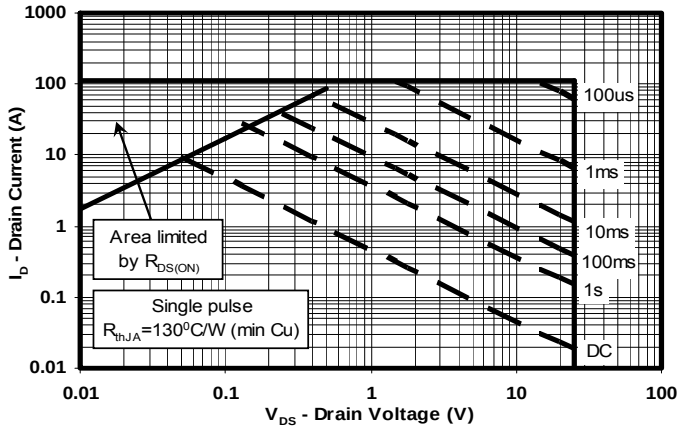


Figure 10: Maximum Safe Operating Area

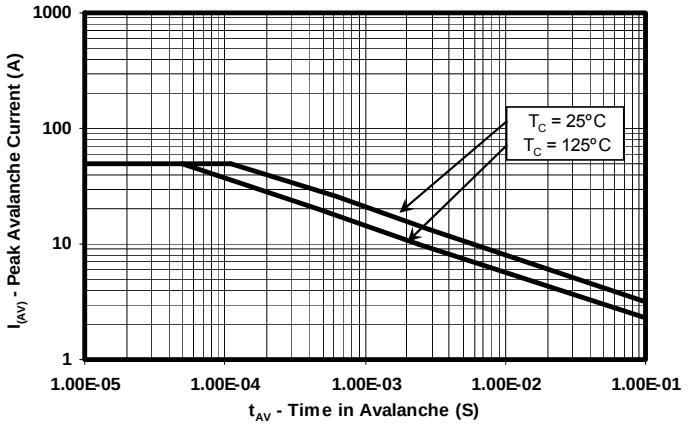


Figure 11: Single Pulse Unclamped Inductive Switching

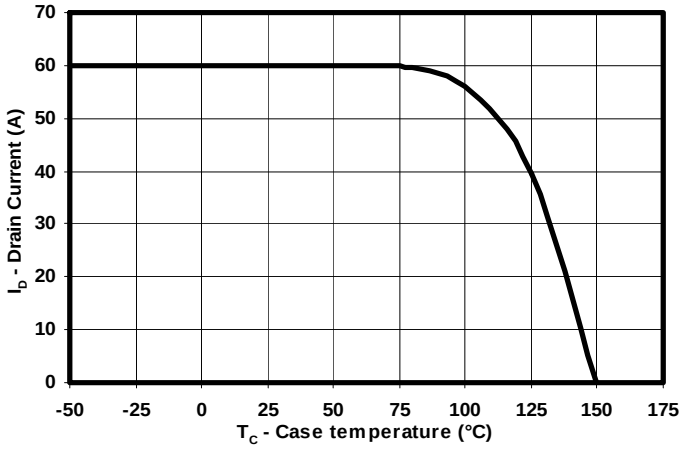
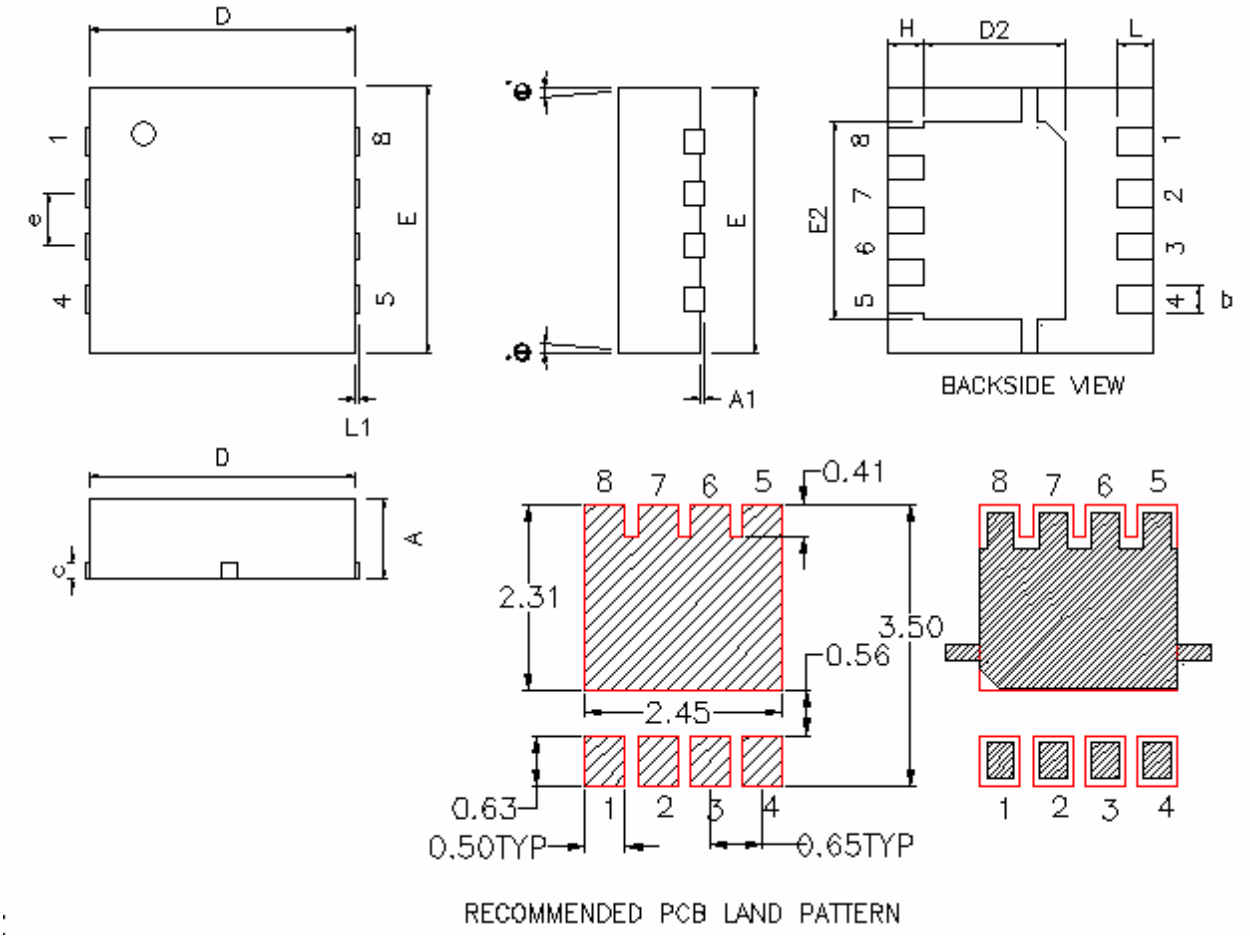


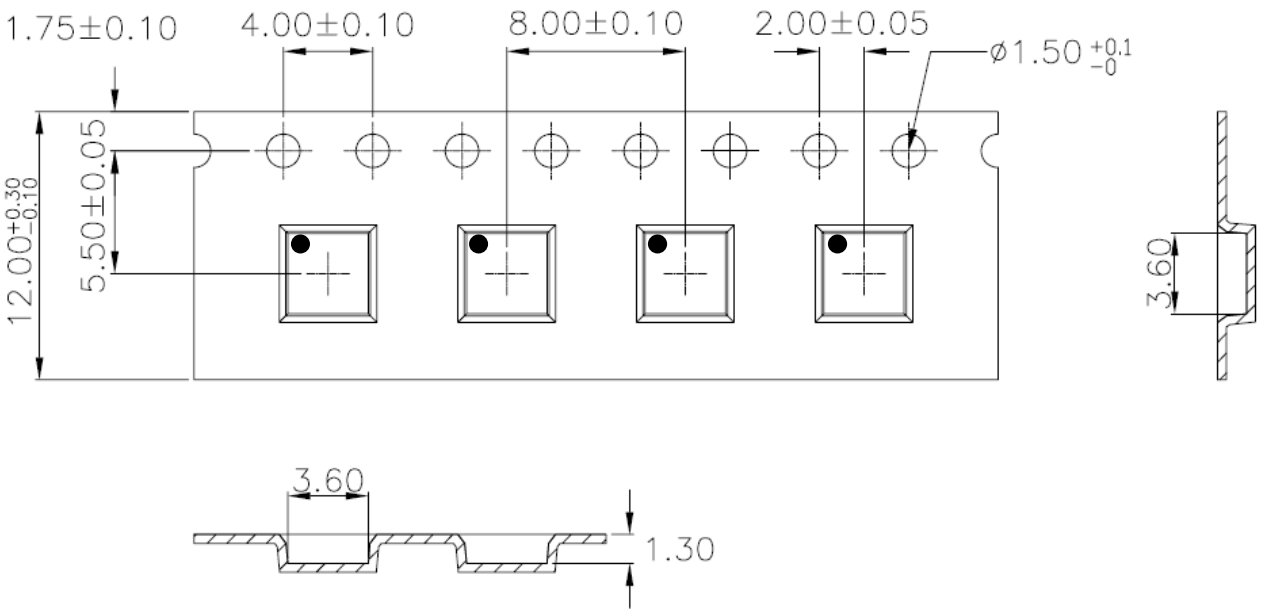
Figure 12: Maximum Drain Current vs. Temperature

CSD16406Q3 Package Dimensions



DIM	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.950	1.000	1.100	0.037	0.039	0.043
A1	0.000	0.000	0.050	0.000	0.000	0.002
b	0.280	0.340	0.400	0.011	0.013	0.016
c	0.150	0.200	0.250	0.006	0.008	0.010
D	3.200	3.300	3.400	0.126	0.130	0.134
D1	-	-	-	-	-	-
D2	1.650	1.750	1.800	0.065	0.069	0.071
E	3.200	3.300	3.400	0.126	0.130	0.134
E1	-	-	-	-	-	-
E2	2.350	2.450	2.550	0.093	0.096	0.100
e	0.650 TYP			0.026		
H	0.35	0.450	0.550	0.014	0.018	0.022
L	0.35	0.450	0.550	0.014	0.018	0.022
L1	-	-	-	-	-	-
θ	-	-	-	-	-	-

Q3 Tape and Reel Information



Note:

1. 10 SPROCKET HOLE PITCH CUMULATIVE TOLERANCE +/-0.2
2. CAMBER NOT TO EXCEED 1mm IN 100mm, NONCUMULATIVE OVER 250mm
3. MATERIAL:BLACK STATIC DISSIPATIVE POLYSTYRENE
4. ALL DIMENSIONS ARE IN mm (UNLESS OTHERWISE SPECIFIED)
5. THICKNESS: 0.30 +/-0.05mm

Package Marking Information

Location:

1st Line

CSD = Fixed Characters

NNNNN = Product Code

2nd Line (Date Code)

YY = Last 2 digits of the Year

WW = 2-digit Work Week

C = Country of Origin

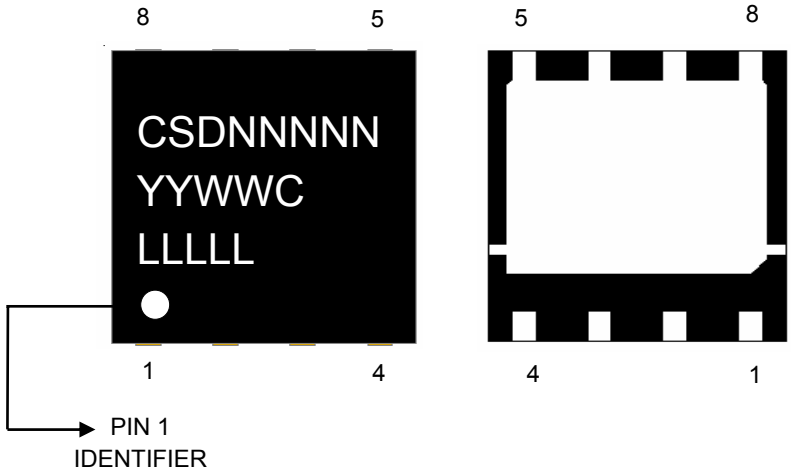
> Philippines = P

> Taiwan = T

> China = C

3rd Line

LLLLL= Last 5 digits of the Wafer Lot #



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